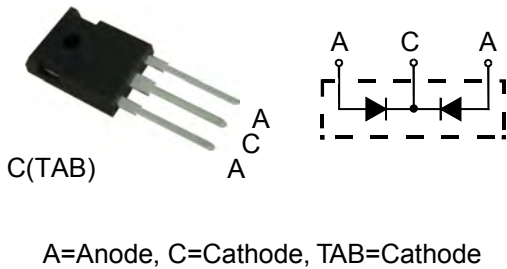
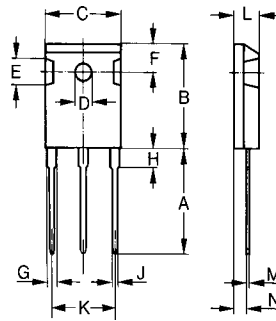


# HUR3060PT

Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes



Dimensions TO-247AD



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	19.81	20.32	0.780	0.800
B	20.80	21.46	0.819	0.845
C	15.75	16.26	0.610	0.640
D	3.55	3.65	0.140	0.144
E	4.32	5.49	0.170	0.216
F	5.4	6.2	0.212	0.244
G	1.65	2.13	0.065	0.084
H	-	4.5	-	0.177
J	1.0	1.4	0.040	0.055
K	10.8	11.0	0.426	0.433
L	4.7	5.3	0.185	0.209
M	0.4	0.8	0.016	0.031
N	1.5	2.49	0.087	0.102

	V <sub>RSM</sub>	V <sub>RRM</sub>
	V	V
<b>HUR3060PT</b>	600	600

Symbol	Test Conditions	Maximum Ratings	Unit
I <sub>FRMS</sub> I <sub>FAVM</sub>	T <sub>C</sub> =140°C; rectangular, d=0.5	35 2 x 15	A
I <sub>FSM</sub>	T <sub>VJ</sub> =45°C; t <sub>p</sub> =10ms (50Hz), sine	110	A
E <sub>AS</sub>	T <sub>VJ</sub> =25°C; non-repetitive; I <sub>AS</sub> =1A; L=180uH	0.1	mJ
I <sub>AR</sub>	V <sub>A</sub> =1.5·V <sub>R</sub> typ.; f=10kHz; repetitive	0.1	A
T <sub>VJ</sub> T <sub>VJM</sub> T <sub>stg</sub>		-55...+175 175 -55...+150	°C
P <sub>tot</sub>	T <sub>C</sub> =25°C	95	W
M <sub>d</sub>	mounting torque	0.4...0.6	Nm
Weight	typical	6	g

**Sirectifier**®

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Symbol	Test Conditions	Characteristic Values		Unit
		typ.	max.	
<b>I<sub>R</sub></b>	T <sub>VJ</sub> =25°C; V <sub>R</sub> =V <sub>RRM</sub> T <sub>VJ</sub> =150°C; V <sub>R</sub> =V <sub>RRM</sub>		100	uA
			0.5	mA
<b>V<sub>F</sub></b>	I <sub>F</sub> =15A; T <sub>VJ</sub> =150°C T <sub>VJ</sub> =25°C		1.35	V
			2.04	
<b>R<sub>thJC</sub></b> <b>R<sub>thCH</sub></b>		0.5	1.6	K/W
<b>t<sub>rr</sub></b>	I <sub>F</sub> =1A; -di/dt=100A/us; V <sub>R</sub> =30V; T <sub>VJ</sub> =25°C	35		ns
<b>I<sub>RM</sub></b>	V <sub>R</sub> =100V; I <sub>F</sub> =25A; -di <sub>F</sub> /dt=100A/us; T <sub>VJ</sub> =100°C		4.9	A

## FEATURES

- \* International standard package
- \* Glass passivated chips
- \* Very short recovery time
- \* Extremely low switching losses
- \* Low I<sub>RM</sub>-values
- \* Soft recovery behaviour
- \* RoHS compliant

## APPLICATIONS

- \* Antiparallel diode for high frequency switching devices
- \* Antisaturation diode
- \* Snubber diode
- \* Free wheeling diode in converters and motor control circuits
- \* Rectifiers in switch mode power supplies (SMPS)
- \* Inductive heating
- \* Uninterruptible power supplies (UPS)
- \* Ultrasonic cleaners and welders

## ADVANTAGES

- \* Avalanche voltage rated for reliable operation
- \* Soft reverse recovery for low EMI/RFI
- \* Low I<sub>RM</sub> reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

**Sirectifier**®

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Soft Recovery Behaviour High-Performance Wide Temperature Range Ultra Fast Recovery Epitaxial Diodes

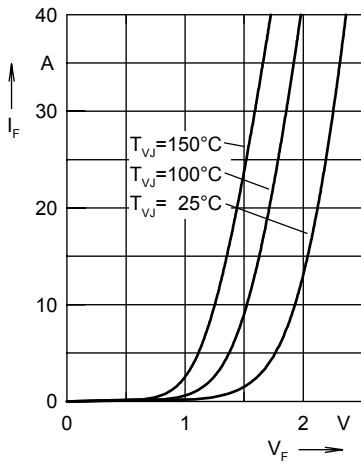


Fig. 1 Forward current  $I_F$  versus  $V_F$

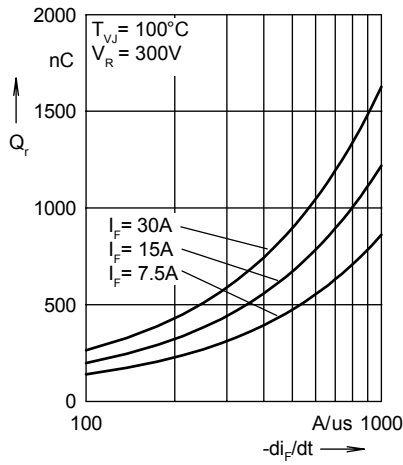


Fig. 2 Reverse recovery charge  $Q_r$  versus  $-di_F/dt$

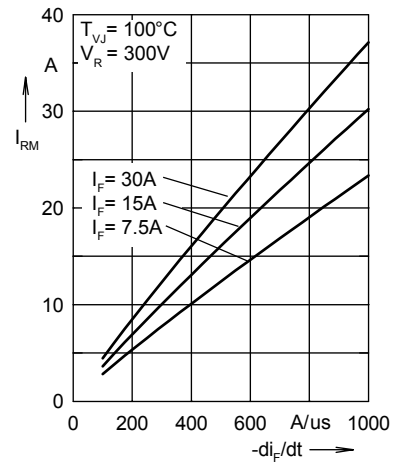


Fig. 3 Peak reverse current  $I_{RM}$  versus  $-di_F/dt$

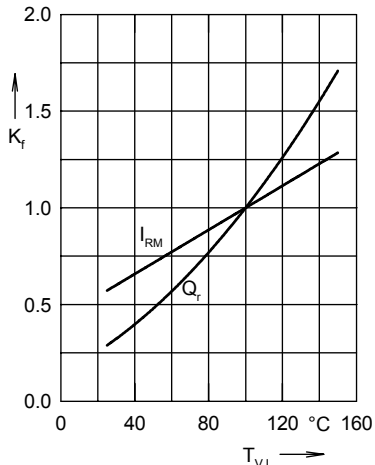


Fig. 4 Dynamic parameters  $Q_r$ ,  $I_{RM}$  versus  $T_{VJ}$

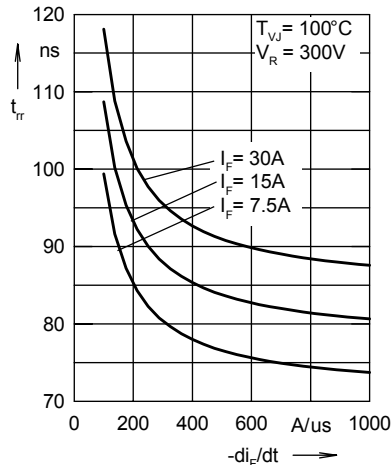


Fig. 5 Recovery time  $t_{tr}$  versus  $-di_F/dt$

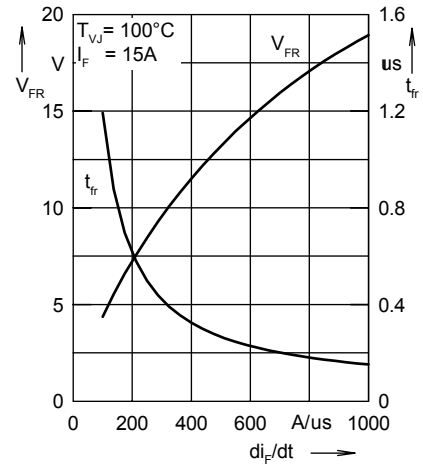


Fig. 6 Peak forward voltage  $V_{FR}$  and  $t_{tr}$  versus  $di_F/dt$

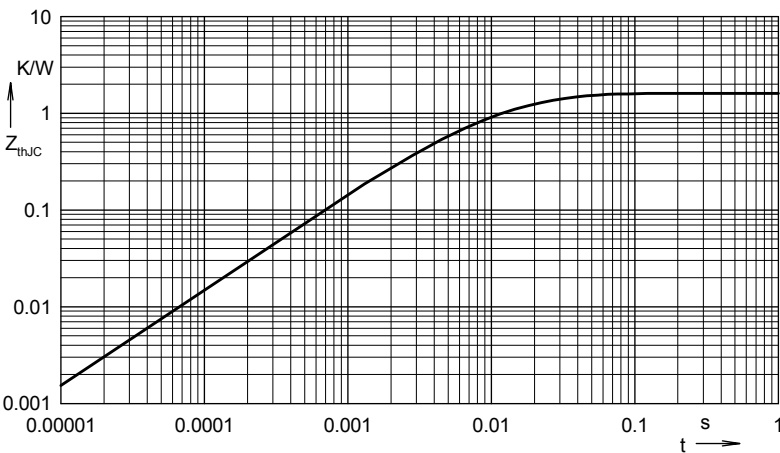


Fig. 7 Transient thermal resistance junction to case

Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.908	0.0052
2	0.35	0.0003
3	0.342	0.017